TO-252 N MOS
N-CHANNEL MOSFET in a TO-252 Plastic Package.

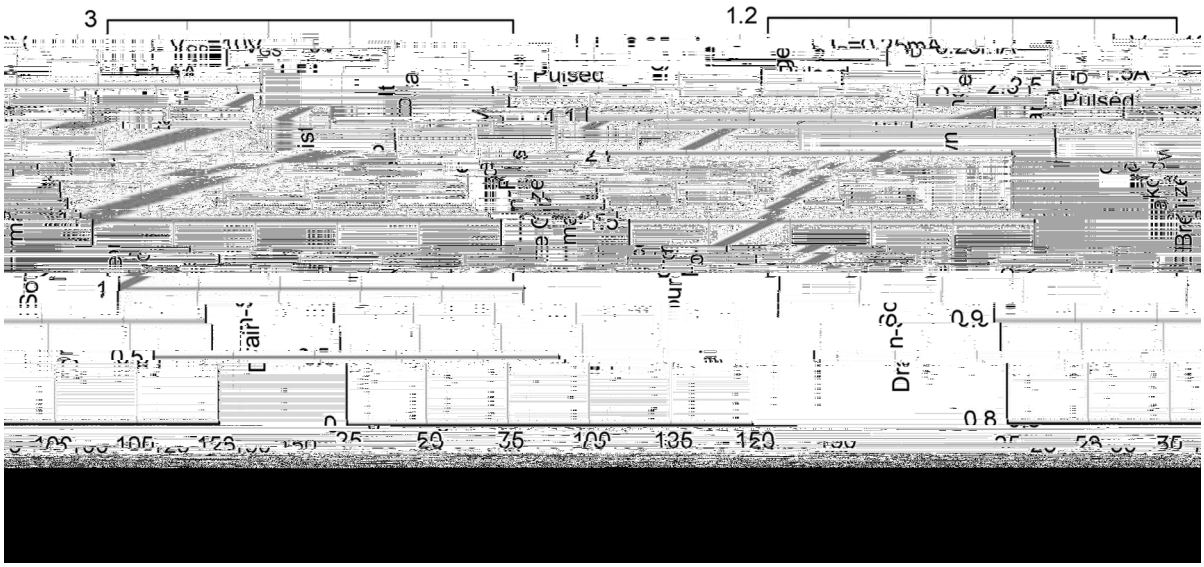
Ң /Ң / /
Low gate charge, low crss, fast switching,HF Product. Have good Electromagnetic Interference performance, HF Product.

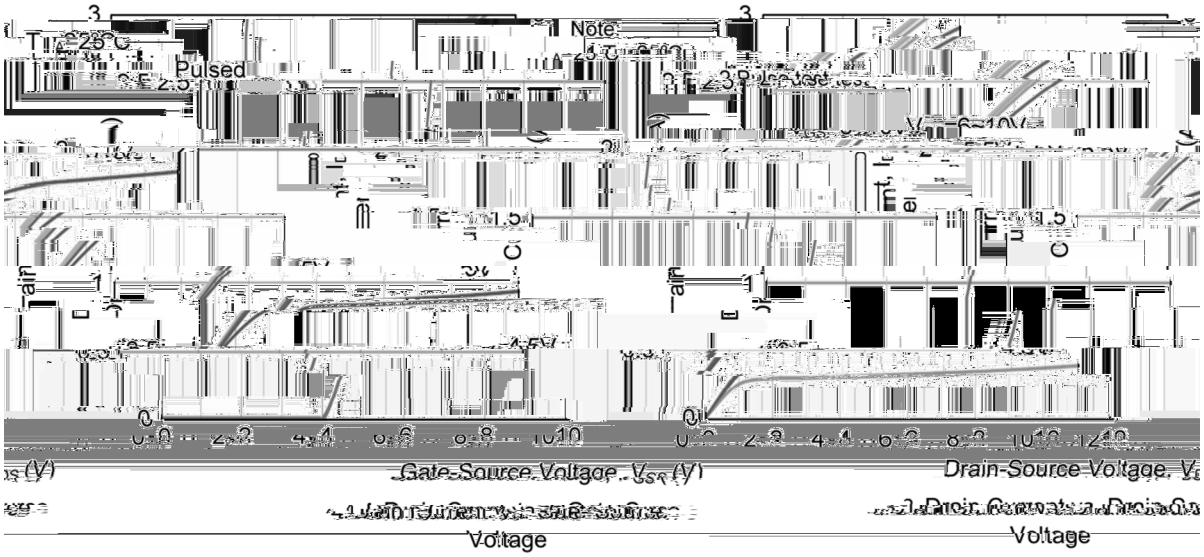
These devices are well suited for power switch circuit of adaptor and charger.

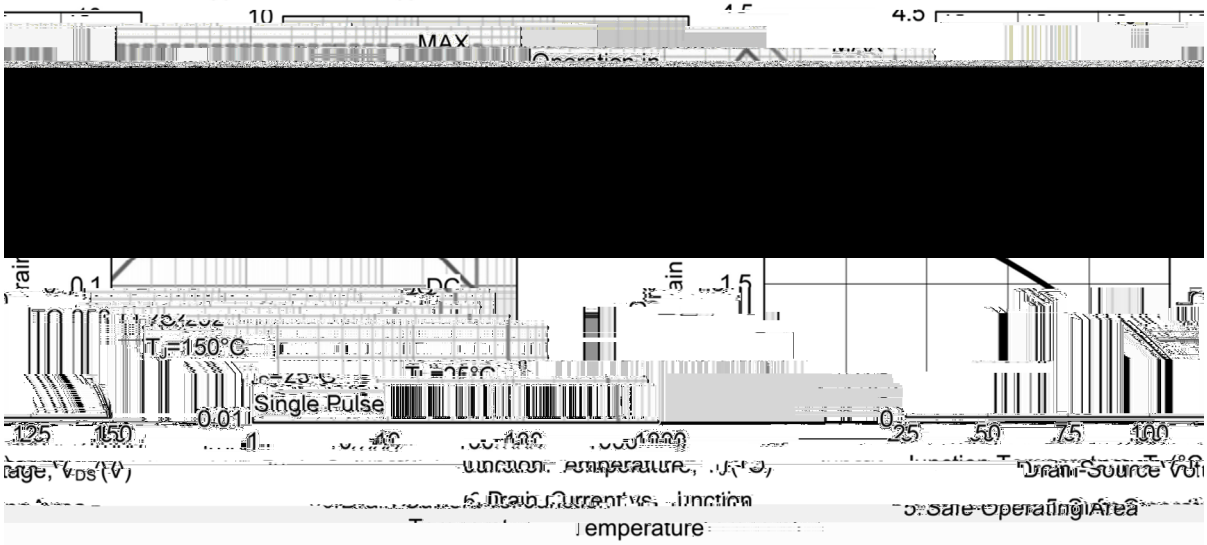
PIN1 G PIN 2 D PIN 3

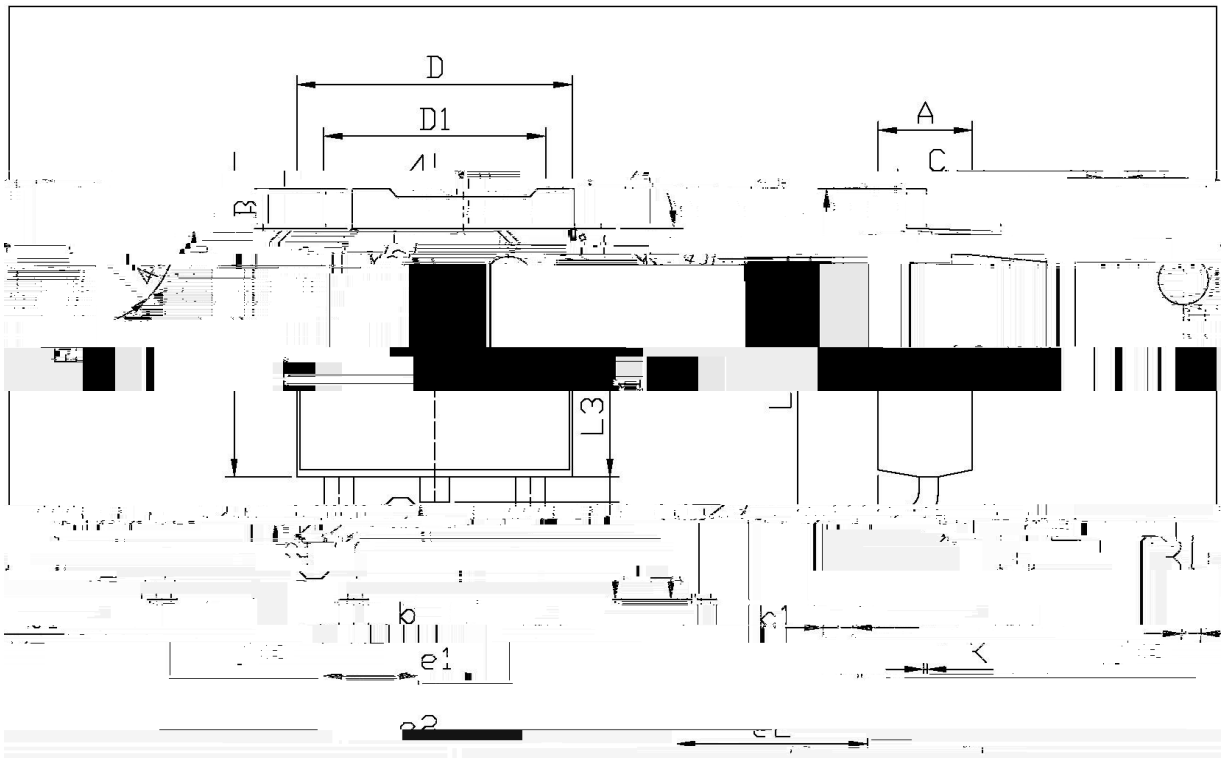
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	500	V
Drain Current	I_D(Tc=25)	3	A
Drain Current - Pulsed	I_{DM}	6	A
Gate-Source Voltage	V_{GS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	97	mJ
Avalanche Current	I_{AS}	4.4	A
Power Dissipation	P_D(Tc=25)	45	W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	td(on)	V_{DD}=100V I_D=3.0A V_{GS}=10V R_G=25Ω		4		ns


Pulsed
Pulsed


Note:
Pulsed
Gate-Source Voltage
Drain-Source Voltage
Voltage
Voltage


MAX
DC
Single Pulse
Drain-Source Voltage
Junction Temperature
Safe Operating Area
Temperature

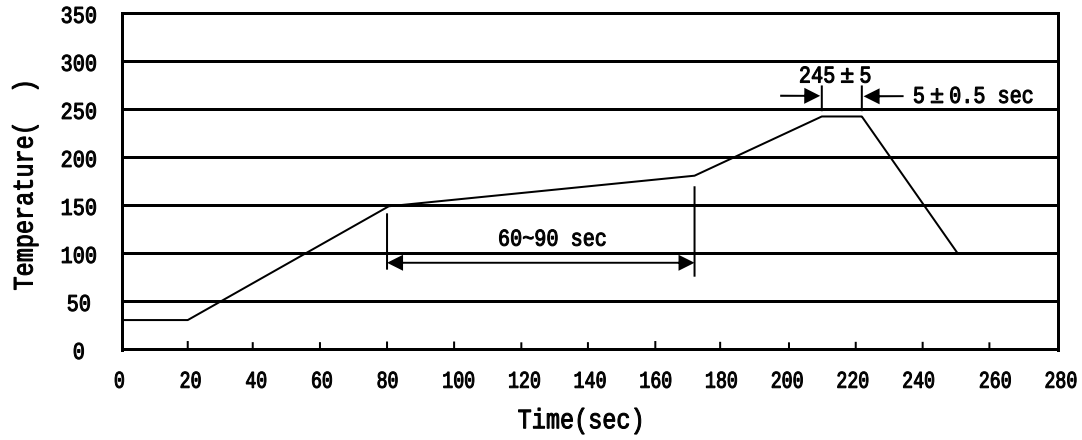


单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
B	0.95	1.25	e	2.24	2.34
	0.79	0.90			
	0.55			0.95	1.35
	0.45	0.55			
	6.45	6.75		0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252

Temperature Profile for IR Reflow Soldering(Pb-Free)



		Note:	
1	150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.	
2	245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.	
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.	

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ REEL

Package Type	Units					Dimension		(unit mm³)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	6	30,000	13 ×16	360×360×50	380×335×366

/ TUBE

Package Type	Units					Dimension		(unit mm³)
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180